



Fast Crystal Scintillators for GHz Hard X-Ray Imaging

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Presentation in the ULITIMA 2018 Conference at ANL



GHz Hard X-Ray Imaging



High-Energy and Ultrafast X-Ray Imaging Technologies and Applications

Organizers: Peter Denes, Sol Gruner, Michael Stevens & Zhehui (Jeff) Wang¹ (Location/Time: Santa Fe, NM, USA /Aug 2-3, 2016)

The goals of this workshop are to gather the leading experts in the related fields, to prioritize tasks for ultrafast hard X-ray imaging detector technology development and applications in the next 5 to 10 years, see Table 1, and to establish the foundations for near-term R&D collaborations.

Performance	Type I imager	Type II imager		
X-ray energy	30 keV	42-126 keV		
Frame-rate/inter-frame time	0.5 GHz/2 ns	3 GHz / 300 ps		
Number of frames	10	10 - 30		
X-ray detection efficiency	above 50%	above 80%		
Pixel size/pitch	≤ 300 μm	< 300 μm		
Dynamic range	10 ³ X-ray photons	≥ 10 ⁴ X-ray photons		
Pixel format	64 x 64 (scalable to 1 Mpix)	1 Mpix		

Table I. High-energy photon imagers for MaRIE XFEL

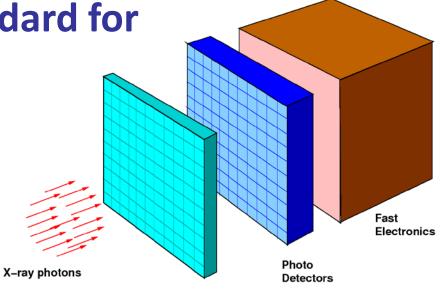
2 ns and 300 ps inter-frame time requires very fast scintillator and sensor



Why Crystal Scintillator?



- Detection efficiency for hard X-ray requires bulk detector.
- Scintillation light provides fast signal.
- Pixelized crystal detector is a standard for medical industry.
- A detector concept:
 - Pixelized fast scintillator screen;
 - Pixelized fast photodetector;
 - Fast electronics readout.
- Challenges:



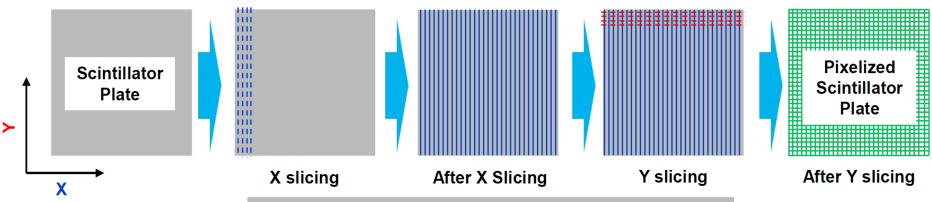
Fast Scintillator Screen

Ultra-fast crystals, photodetectors and readout.



Pixelized Crystal Detectors

Crystal panels of 300 μ pitch may be fabricated by classical mechanical processing



A Schematic showing pixelized scintillator plate processing





Presentation by Liyuan Zhang, Caltech, in the ULITIMA 2018 Conference at ANL



Candidate Scintillators for Marie

	LYSO (:Ce)	YSO:Ce	ZnO:Ga	BaF ₂	BaF ₂ :Y	YAP:Ce	YAP:Yb	YAG:Yb	LuAG:Ce	LaBr₃ (:Ce)
Density (g/cm ³)	7.4	4.44	5.67	4.89	4.89	5.35	5.35	4.56	6.76	5.29
Melting points (°C)	2050	2070	1975	1280	1280	1870	1870	1940	2060	783
X ₀ (cm)	1.14	3.10	2.51	2.03	2.03	2.77	2.77	3.53	1.45	1.88
R _M (cm)	2.07	2.93	2.28	3.1	3.1	2.4	2.4	2.76	2.15	2.85
λ _ι (cm)	20.9	27.8	22.2	30.7	30.7	22.4	22.4	25.2	20.6	30.4
Z _{eff}	64.8	33.3	27.7	51.6	51.6	31.9	31.9	30	60.3	45.6
dE/dX (MeV/cm)	9.55	6.57	8.42	6.52	6.52	8.05	8.05	7.01	9.22	6.90
λ _{peak} ª (nm)	420	420	389	300 220	300 220	370	350	350	520	360
Refractive Index ^b	1.82	1.78	2.1	1.50	1.50	1.96	1.96	1.87	1.84	1.9
Normalized Light Yield ^{a,c}	100	80	6.6 ^e	42 4.8	1.7 4.8	9 32	0.19 ^e	0.36 ^e	35 ^f 48 ^f	153
Total Light yield (ph/MeV)	30,000	24,000	2,000 ^e	13,000	2,000	12,000	57°	110 ^e	25,000 ^f	46,000
Decay time ^a (ns)	40	75	<1	600 <mark>0.6</mark>	600 <mark>0.6</mark>	191 25	1.5	4	981 ^f 64 ^f	20
Light Yield in 1 st ns (photons/MeV)	740	318	610 ^e	1200	1200	391	28 ^e	24 ^e	240	2,200
40 keV Att. Length (1/e, mm)	0.185	0.334	0.407	0.106	0.106	0.314	0.314	0.439	0.251	0.131

[1] Spurrier, et al., *IEEE T. Nucl. Sci.* 2008,55 (3): 1178-1182.

a. Top line: slow component, bottom line: fast component;

b. At the wavelength of the emission maximum;

c. Excited by Gamma rays;

d. For 0.4 at% Ca co-doping;

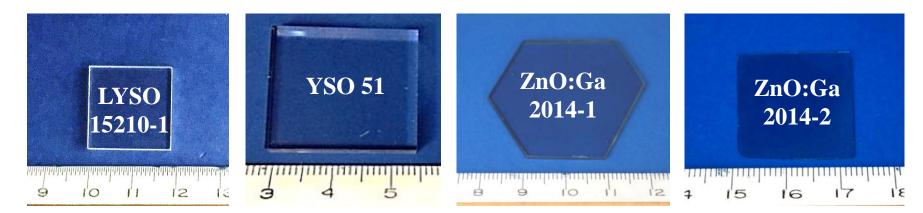
e. Excited by Alpha particles.

f. Ceramic with 0.3 Mg at% co-doping



LYSO and ZnO:Ga Samples





Crystal	Vendor	ID	Dimension (mm ³)
LYSO:Ce	SIC	150210-1	19x19×2
YSO:Ce	SIC	51	25×25×5
ZnO:Ga	FJIRSM	2014-1	33×30×2
ZnO:Ga	FJIRSM	2014-2	22×22×0.3

Experiments

 Properties measured at room temperature : PL & Decay, Transmittance, PHS, LO & Decay kinetics

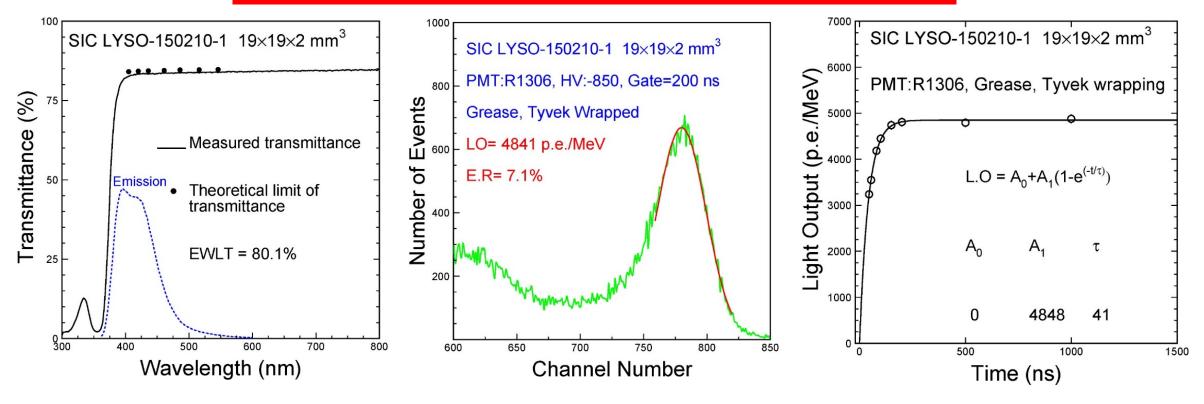


SIC LYSO:Ce-150210-1



✓ High LO, good transmittance and ER, short decay time

× Decay time too long for X-ray frame rate of a few ns



ID	Dimension	EWLT (%)	ER (%)	200 ns LO (p.e./MeV)	Primary Decay Time (ns)	
SIC LYSO-150210-1	19×19×2	80.1	7.1	4841	41	



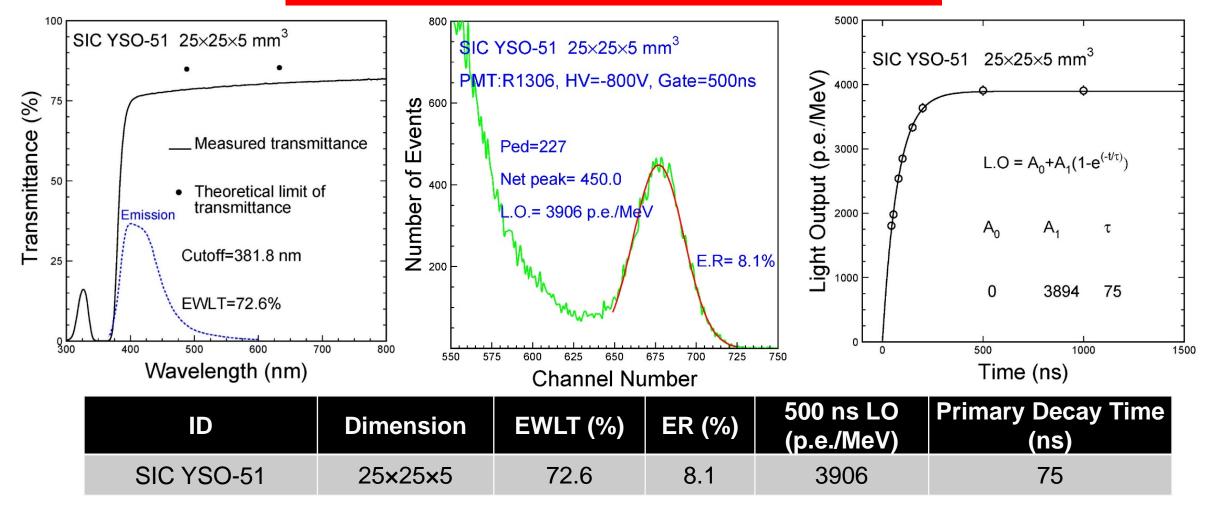
X

SIC YSO:Ce-51 (in LANL)



Good LO, transmittance, ER, and short decay time

All these performance are inferior to LYSO:Ce



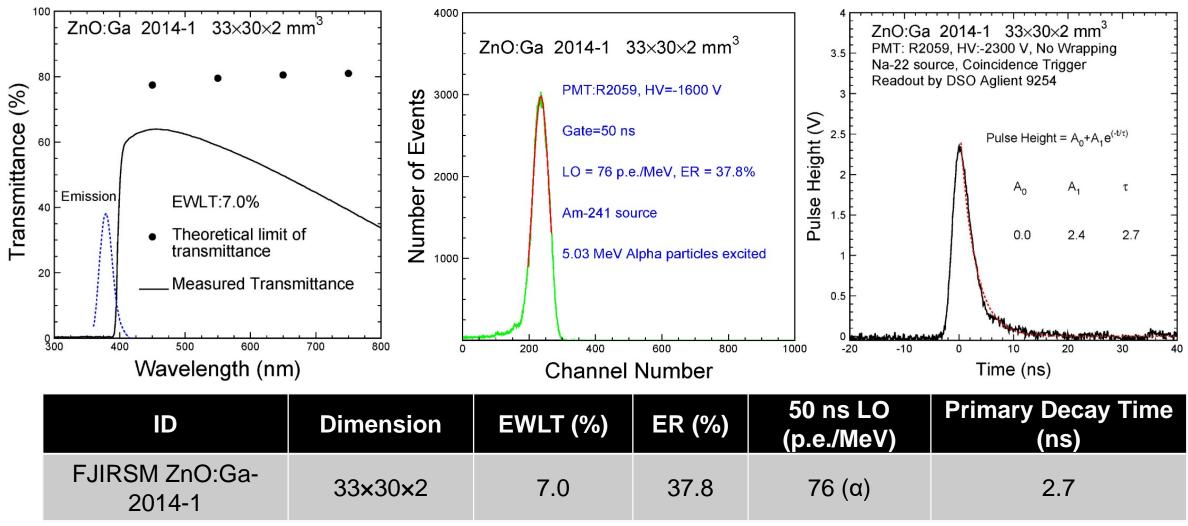


FJIRSM ZnO:Ga-2014-1

Very short decay time



× Low EWLT and LO due to severe self absorption



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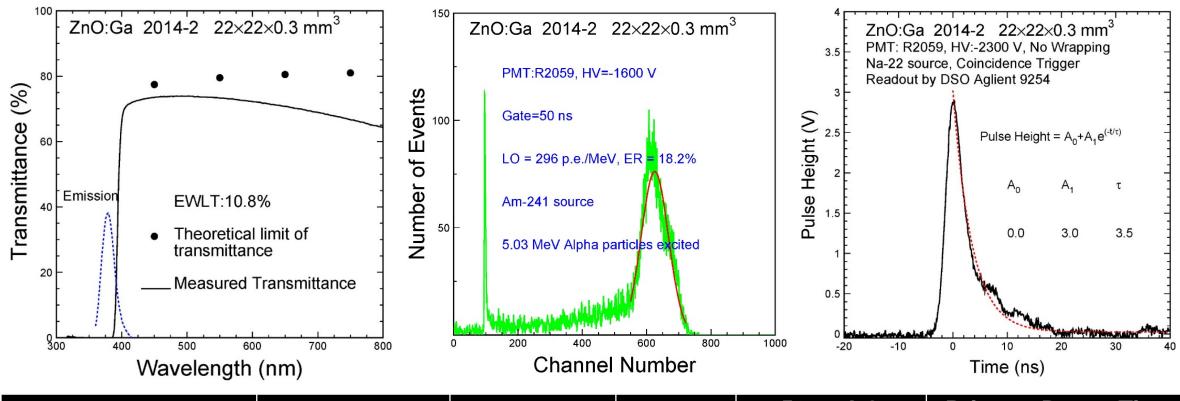


FJIRSM ZnO:Ga-2014-2



× Reduced self absorption due to 0.3 mm thickness

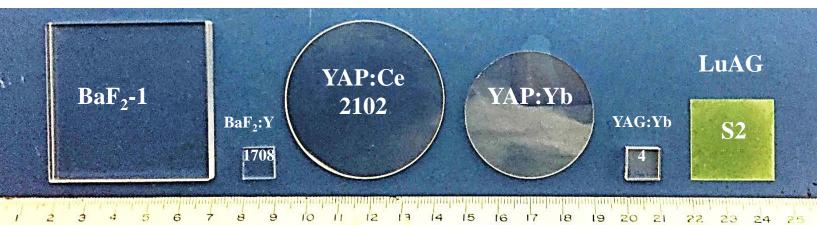
× May pursue QD, NP or thin film based solution



ID	Dimension	EWLT (%)	ER (%)	50 ns LO (p.e./MeV)	Primary Decay Time (ns)
FJIRSM ZnO:Ga- 2014-2	22×22×0.3	10.8	18.2	296 (α)	3.5



BaF₂ and Other Samples



Crystal	Vendor	ID	Dimension (mm ³)
BaF ₂	SIC	1	50×50×5
BaF ₂ :Y	BGRI	1708	10×10×2
YAP:Ce	Dongjun	2102	Ф50×2
YAP:Yb	Dongjun	2-2	Ф40×2
YAG:Yb	Dongjun	4	10×10×5
LuAG:Ce	SIC	S2	25×25×0.4

Experiments

 Properties measured at room temperature : PL & Decay, Transmittance, PHS, LO & Decay kinetics

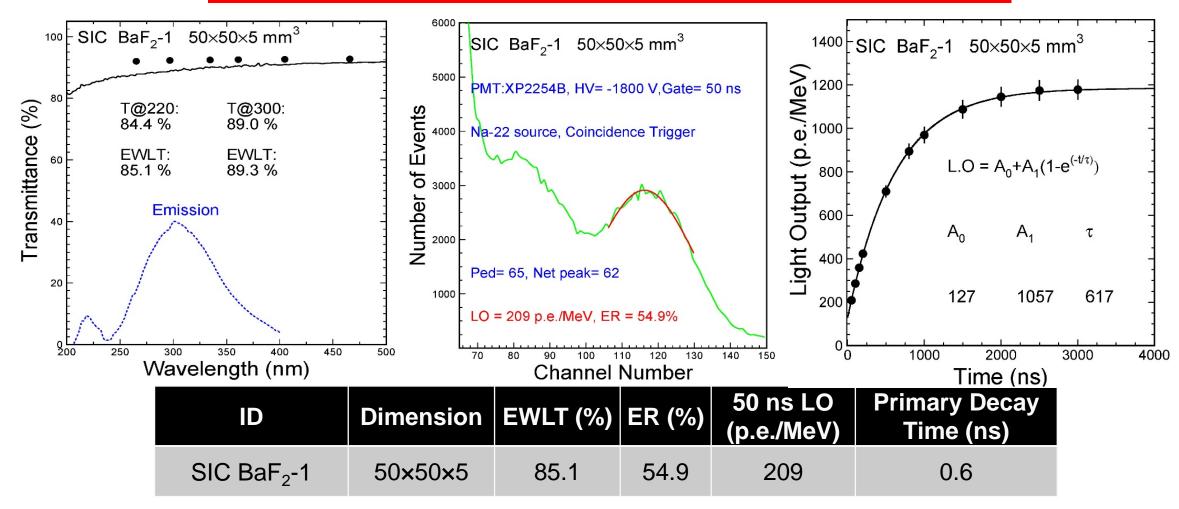






✓ The highest LY in 1st ns among all non-hygroscopic scintillators

× ~600 ns slow component may be suppressed by Y doping

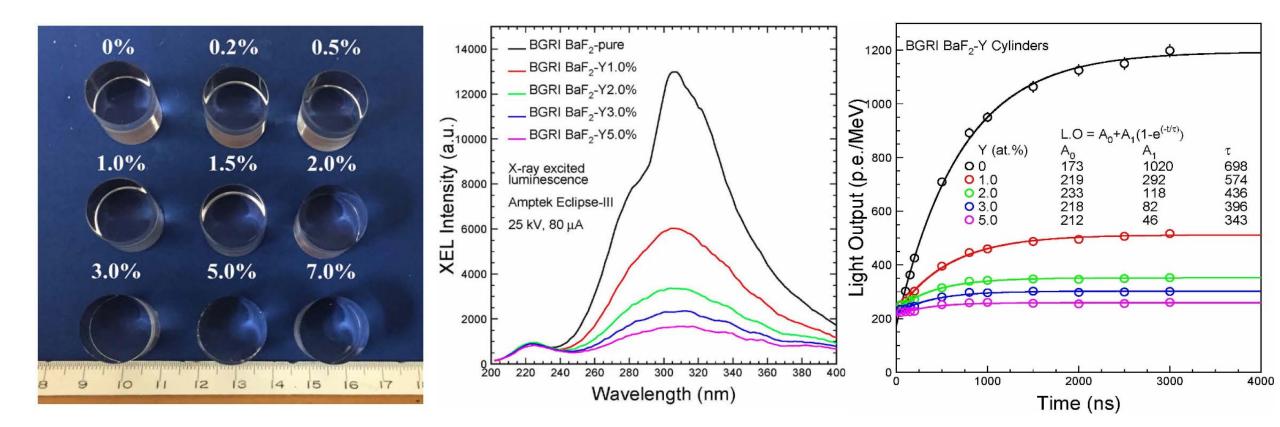




Yttrium Doping in BaF₂



While the fast component in BaF₂ keeps more or less the same, The slow component is significantly suppressed by Yttrium doping.

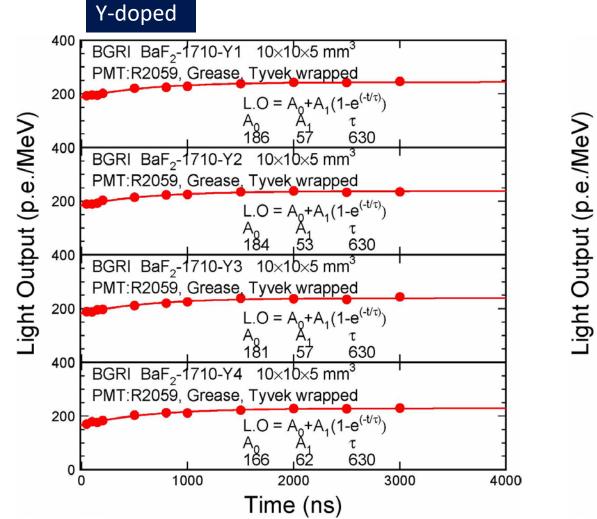




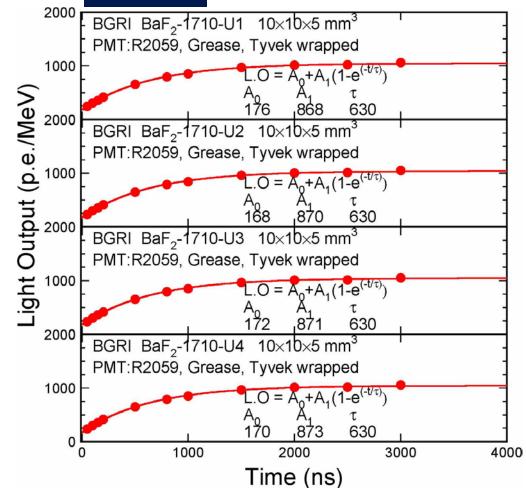
BGRI Y Doped/Undoped BaF₂



Fast/Slow ratio increased from 0.20 to 3.2



Undoped

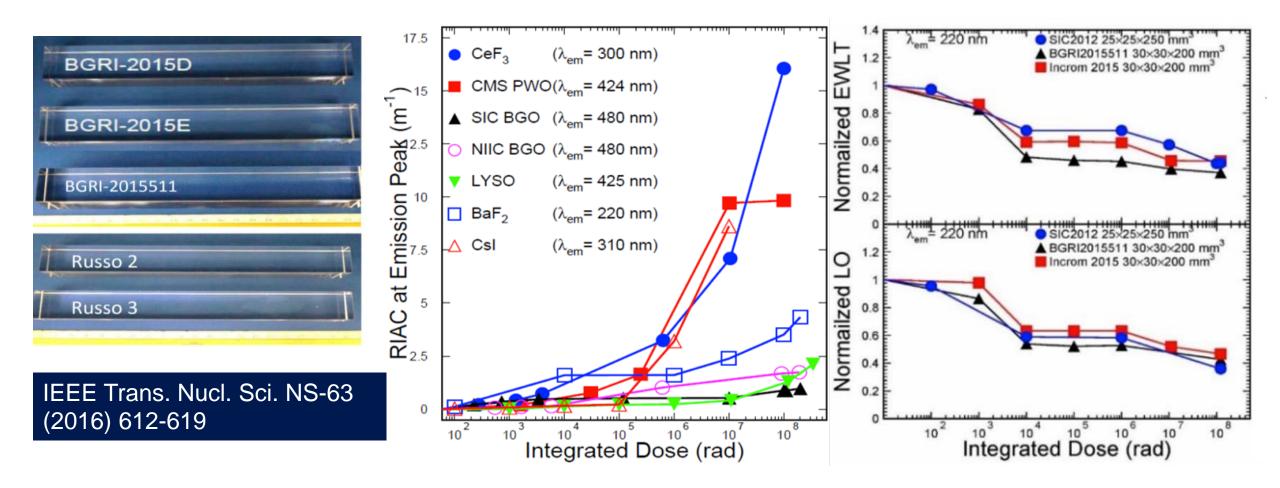




γ-ray induced damage in BaF₂



BaF₂ crystals of 25 cm long were irradiated by Co-60 at Caltech and JPL.
40% fast scintillation light remains after 120 Mrad ionization dose at JPL.

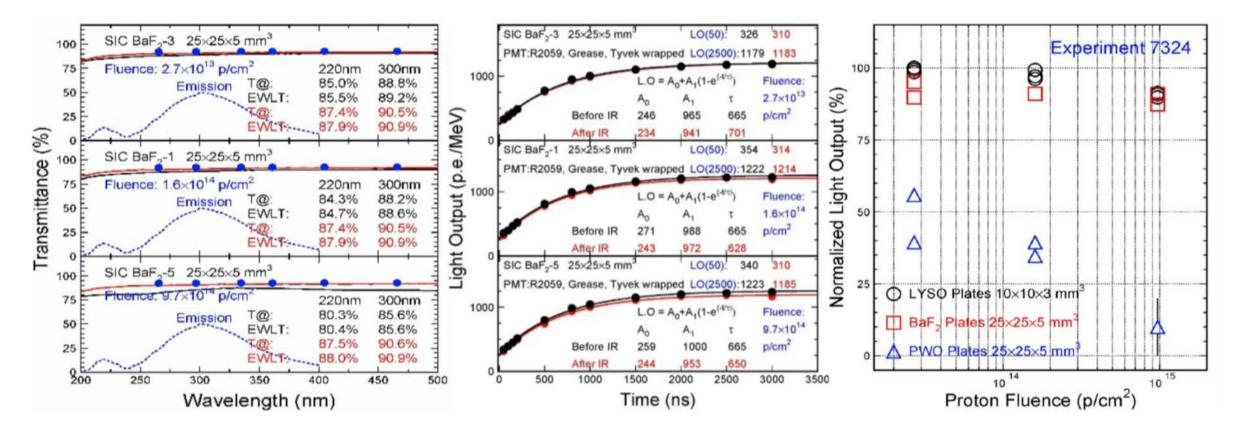




Proton induced damage in BaF₂



BaF₂ plates of 5 mm thick were irradiated by 800 MeV at LANL in 2016. 90% fast scintillation light remains after 10¹⁵ p/cm².



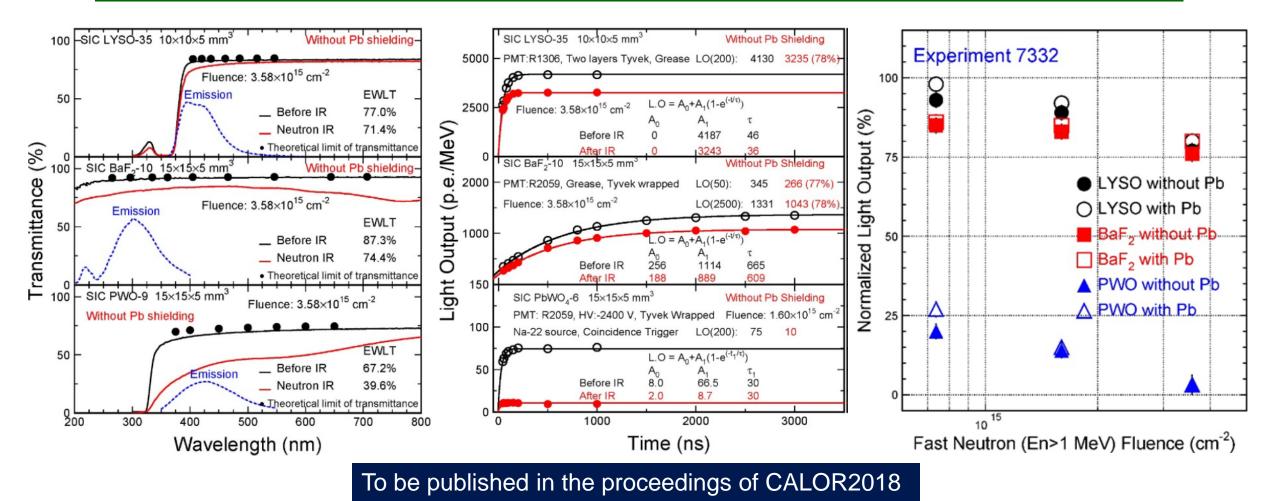
IEEE Trans. Nucl. Sci. NS-65 (2018) 1018-1024



Neutron induced damage in BaF₂



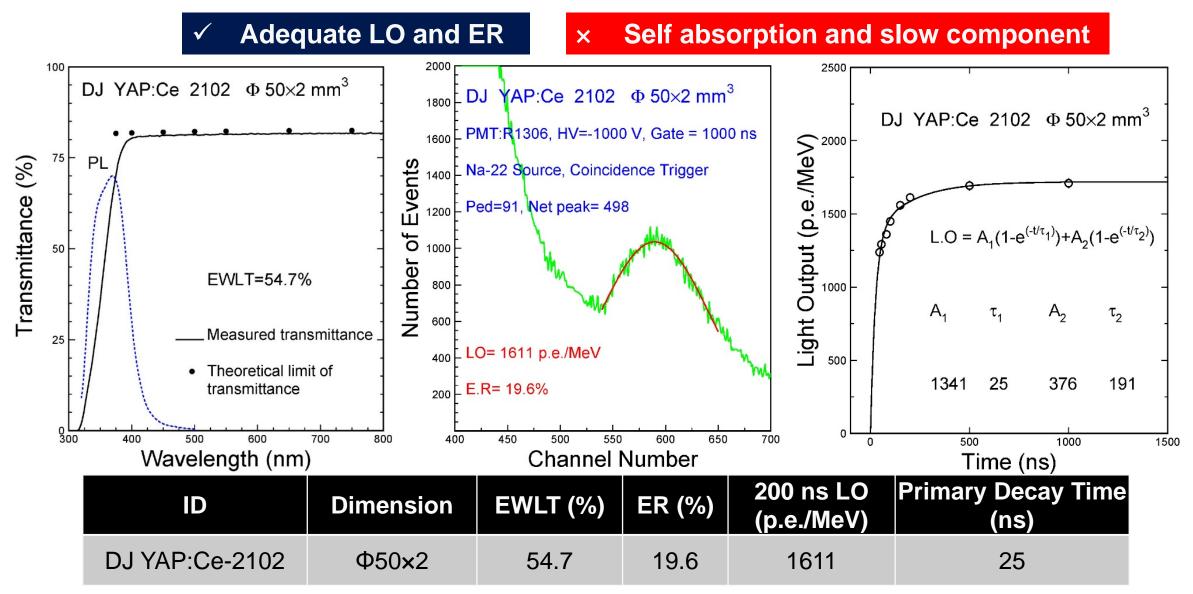
BaF₂ plates of 5 mm thick were irradiated by neutrons at LANL in 2016. 75% fast scintillation light remains after 3×10¹⁵ n (>1 MeV)/cm².





DJ YAP:Ce-2102

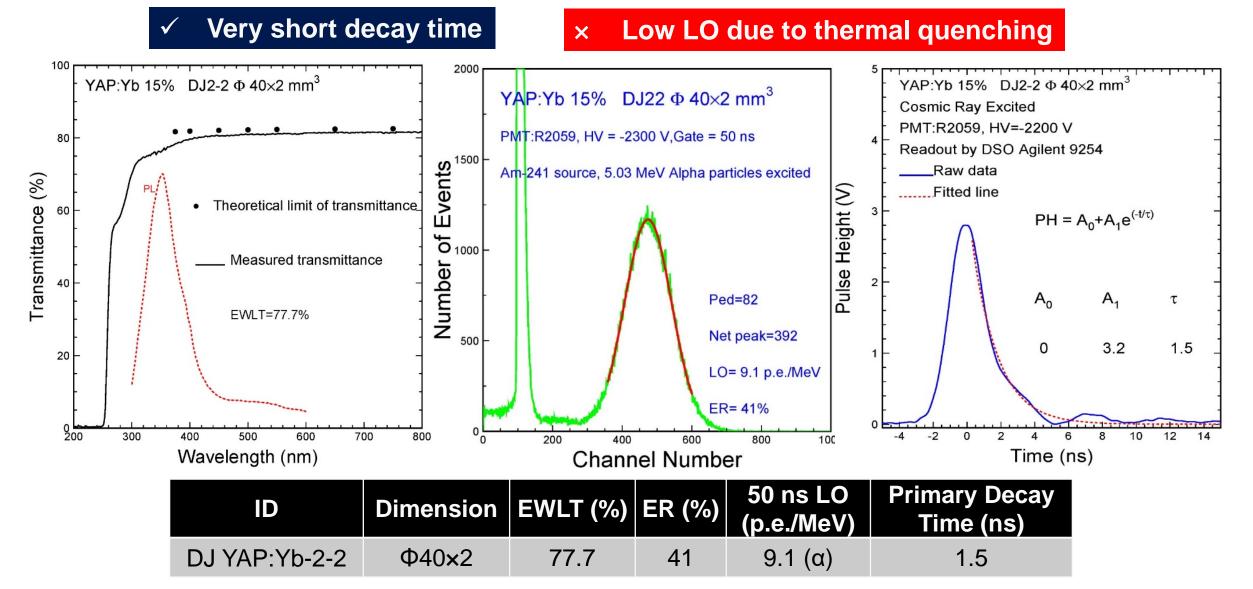






DJ YAP:Yb-2-2





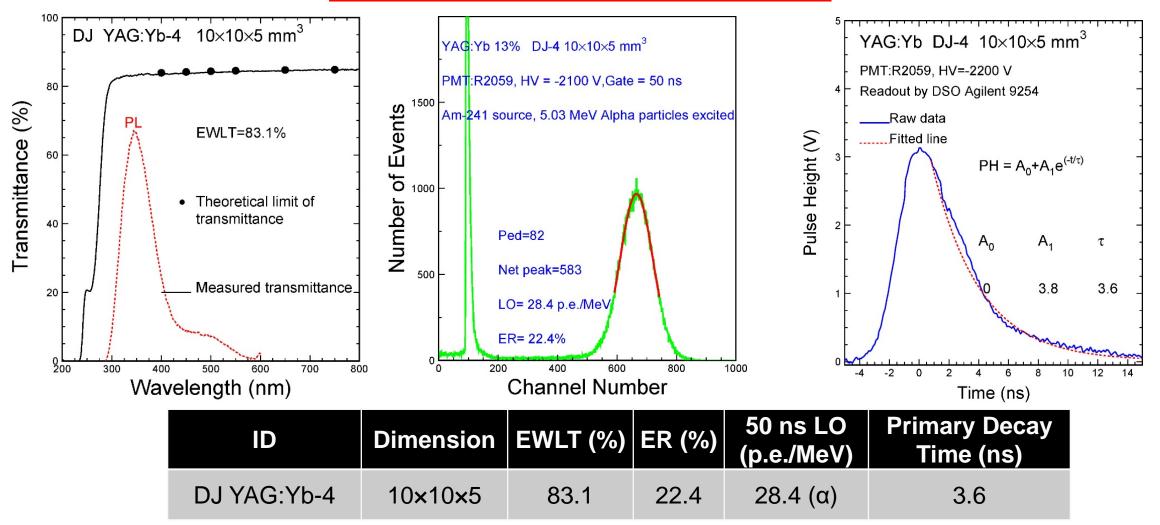






Very short decay time and good transmittance

× Low LO due to thermal quenching





SIC LuAG:Ce-S2 Ceramics



Good LO and ER, and short decay time ~ 1 µs slow component X 2500 LuAG:Ce SIC-S2 25×25×0.4 mm³ LuAG:Ce Ceramics SIC-S2 25×25×0.4 mm³ LuAG:Ce Ceramics SIC-S2 25×25×0.4 mm³ 60 PMT:R1306, 850 V, Two layers Tyvek, Grease Light Output (p.e./MeV) 2000 300 Transmittance (%) Events L.O.=1531, E.R= 19.1% 1500 40 EWLT=52.3% ę 200 L.O = A₁(1-e^(-t/\tau_1))+A₂(1-e^(-t/\tau_2)) Number 1000 Emission 20 A_2 τ_1 τ2 100 500 1325 703 817 51 600 300 400 500 700 350 400 450 800 300 500 2000 0 1000 3000 Wavelength (nm) **Channel Number** Time (ns) 200 ns LO **Primary Decay** EWLT (%) ER (%) Dimension ID Time (ns) (p.e./MeV) SIC LuAG-S2 25×25×0.4 52.3 19.1 1531 51



Multi-layer Detector Concept



Proc. of SPIE Vol. 9504 95040N

A multilayer high QE photocathode coated thin fast scintillators concept was proposed for GHz hard X-ray imaging:

- Spatial resolution determined layer thickness,
- Overall efficiency defined layer number,
- Maximized conversion of scintillation photon to p.e.,
- Magnetic field extraction of p.e. and image preserving,
- Off-beam p.e. multiplication,
- On-board charge storages.

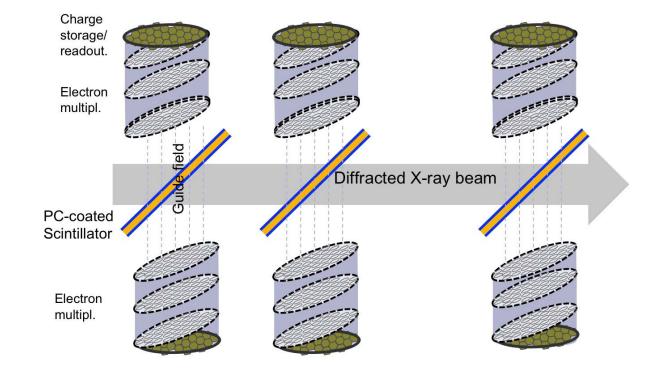
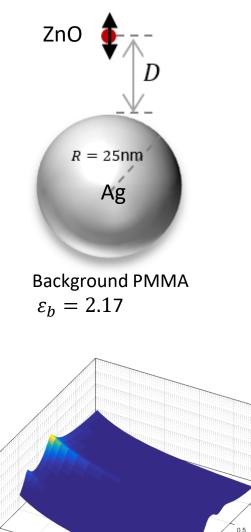


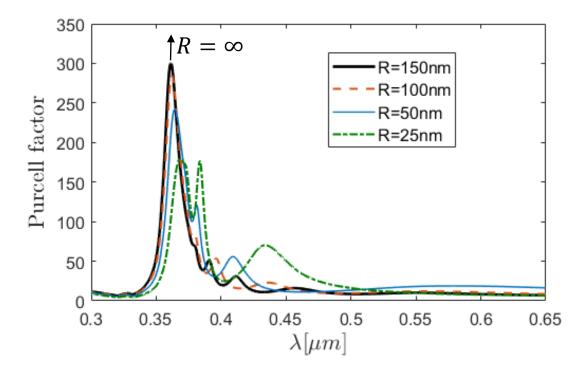
Figure 6. A multi-layer detector architecture for efficient and fast imaging of diffracted X rays. A guide magnetic field perpendicular to the X-ray direction guide the photoelectrons to amplification and storage. The magnetic field also preserves the image contrast due to X-ray absorption at the scintillator location.



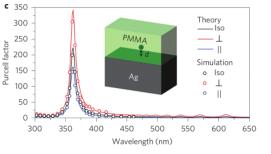
Purcell Factor for Ag Particles



 $D \ [\mu m]$



 $R = \infty$ is equivalent to a infinite layer. Our simulation is greatly agree with experiments (red circles) as right figure. Agreement includes the peak value, wavelength and bandwidth.



-Lu, Dylan, et al. "Enhancing spontaneous emission rates of molecules using Nano patterned multilayer hyperbolic metamaterials." *Nature nanotechnology*9.1 (2014): 48.

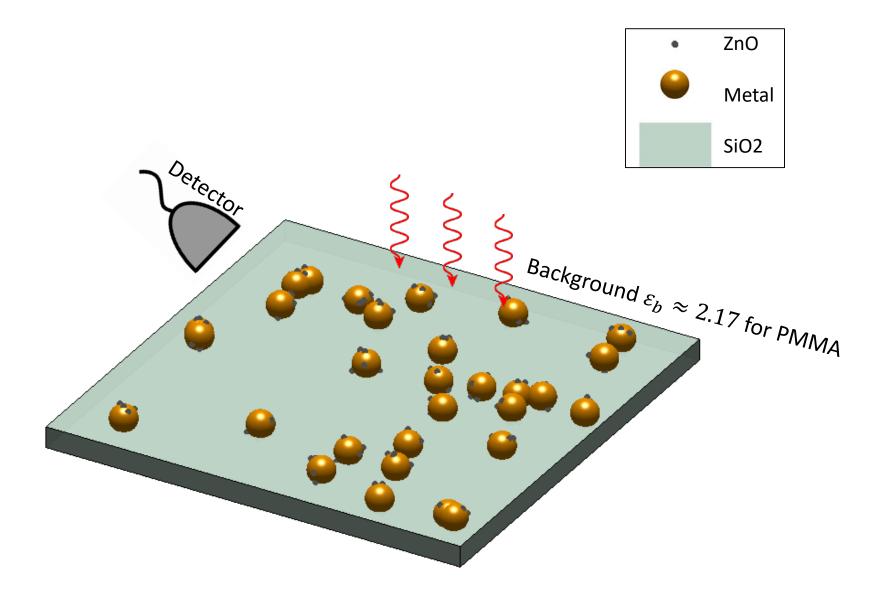
 $\overset{10^4}{}_{10^2} H^{(1)} H^$

Presentation by

 $\lambda[\mu m]$



Experimental Proposal

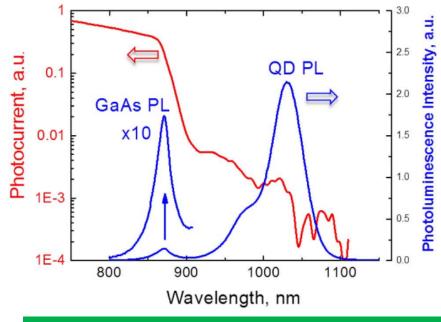




InAs/GaAs QD based Crystal



In recent study^[1], S. Oktyabrsky, et al. report an <u>ultrafast, no self-absorption, high-efficient room-</u> temperature semiconductor scintillator based on InAs QDs embedded in a GaAs matrix.



Room temperature photocurrent spectra overlapped with PL spectra of the same QD structure with reduced wetting layer placed in a p-n junction.

Ref.: [1] S. Oktyabrsky, et al., IEEE Trans. Nucl. Sci. 63, 656 (2016).

Performance of InAs/GaAs Qd Scintillator GaAs/InAs LYSO Parameter BaF₂ QDs Density (g/cm^3) 4.89 7.1 5.32 Radiation length, cm 2.03 1.1 2.3Decay constant, ns 0.8 ns 40 Peak emission, nm 195; 220 428 1050 Photon Yield 1,400 34,000 240,000 (photons/MeV) 2 fs Time between first photons, 0.57ps 1.2 ps for 1MeV Poisson-limited energy 62 13 4.8 resolution at 1MeV (keV) * $10^4 - 10^5$ $10^4 - 10^5$ $>10^{4}$ Radiation hardness, Gy Coupling efficiency <50% <50% ~100%

*Assuming collection efficiency = 1

Comparison of Some Fast Inorganic Scintillators (source: Scintillator.lbl.gov) With Projected



CsPbX₃ (X=Cl, Br and I) QD



It was reported that nanocrystals of cesium lead halide perovskites (CsPbX₃, X = CI, Br,

and I) shows bright emission with a tunable range by quantum size effects.

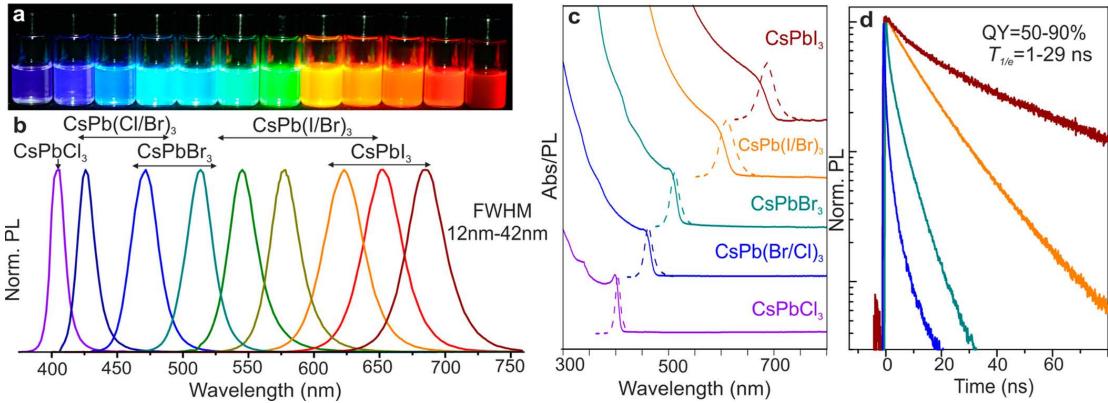


Figure 2. Colloidal perovskite CsPbX3 NCs (X = Cl, Br, I) exhibit size- and composition-tunable bandgap energies covering the entire visible spectral region with narrow and bright emission: (a) colloidal solutions in toluene under UV lamp (λ = 365 nm); (b) representative PL spectra (λ exc = 400 nm for all but 350 nm for CsPbCl3 samples); (c) typical optical absorption and PL spectra; (d) time-resolved PL decays for all samples shown in (c) except CsPbCl3.

Nano Lett. 2015, 15, 3692-3696. DOI: 10.1021/nl5048779



Summary



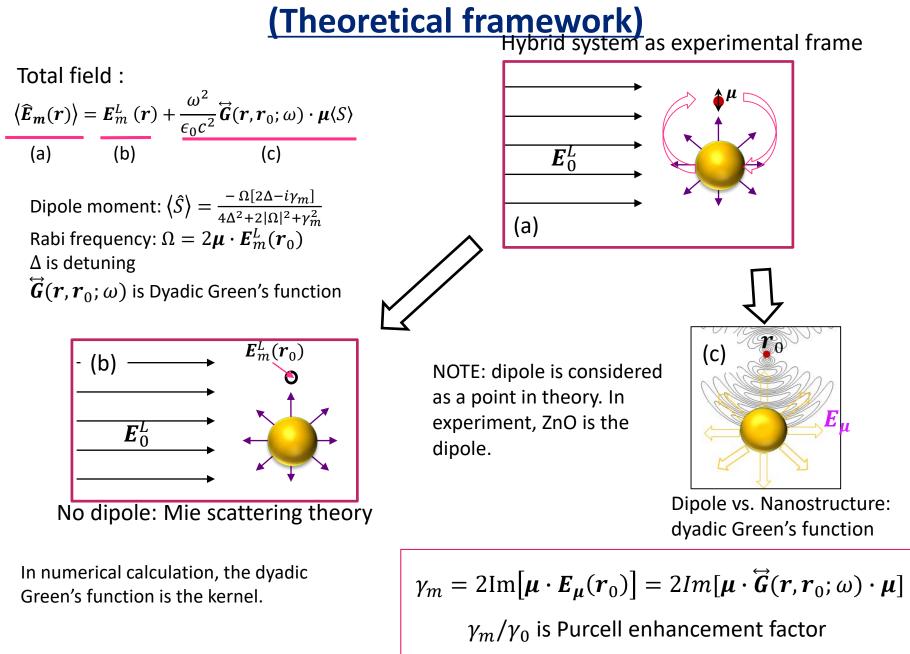
- GHz hard X-ray imaging for the proposed Marie project presents an unprecedented challenge to the speed and radiation hardness of inorganic scintillators.
- BaF₂ crystals provide sufficient fast light with sub-ns decay time and excellent radiation hardness beyond 100 Mrad and 1 x 10¹⁵ h/cm². With its slow component effectively suppressed by yttrium doping BaF₂:Y promises a fast and robust front imager.
- □ Bulk ZnO:Ga crystals suffer from serious self-absorption. Enhanced UV emission in Ag/Au ZnO core-shell nano particles hints a thin film based approach.
- Our plan is to investigate along both lines: BaF₂:Y crystals, and ZnO QD/NP based thin film for the Marie project with a close collaboration between the NP, HEP and material science communities.

Acknowledgements: DOE Award DE-SC001192



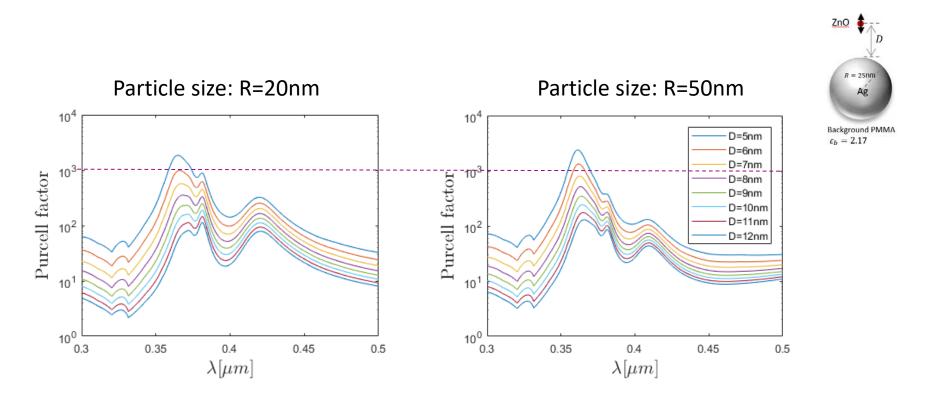
Purcell effect for enhancing ZnO luminescence







Purcell Factor for Ag Particles



- The Purcell factor is sensitive to the distance between ZnO and metallic nanoparticle.
- The bandwidth of Purcell factor is stable for variety of distance D.



The spatial resolution Vs thickness of thin scintillator



Z. Wang et al. has proposed the following equation to determine the maximum thickness of scintillator for a scintillator camera:

$$R_{spatial} = 2dsin\theta_c = 2dsin\frac{1}{n}$$

where $R_{spatial}$ is the spatial resolution, d is the thickness of scintillator, θc is the n is the reflective index of scintillator at emission peak.

- □ The spatial resolution (*R*_{spatial}) of a scintillator camera is limited by the scintillator thickness (d); For an air-to-scintillator interface, the total internal reflection angle (θ_c) is asin(1/n) for a flat interface;
- $R_{spatial}$ is limited to $2dsin\theta_c$ for a thickness d, assuming the light interacts with the interface only once (~ 95% of the light for incidental angles less than the Brewster's angle of atan(1/n)). For 100-µm spatial resolution, the thickness of BaF₂ crystal with a reflective index of 1.54 @220nm cannot exceed 71µm.

The maximum thickness of thin scintillator determined by X-ray imaging spatial resolution										n		
	LYSO:Ce	LSO:Ce,Ca	BaF ₂	CsF	CeBr₃	LaBr₃:Ce	YAG:Yb	YAP:Yb	ZnO:Ga	Pbl ₂	GaAs/In As QDs	Plastic scintillator (BC 404)
Reflective index at emission peak (n)	1.82	1.82	1.54	1.49	1.9	1.9	1.87	1.96	2.1	3.4	3.47	1.58
1/n	0.549	0.549	0.649	0.671	0.526	0.526	0.535	0.510	0.476	0.294	0.288	0.633
atan(1/n)	0.502	0.502	0.576	0.591	0.484	0.484	0.491	0.472	0.444	0.286	0.281	0.564
Maximum thickness (d)for 100um spatial resolution (mm)	86	86	71	68	90	90	89	93	101	167	171	73

Ref.: Z. Wang, C. W. Barnes, J. S. Kapustinsky, C. L. Morris, R. O. Nelson, F. Yang, L. Zhang, and R.-Y. Zhu, Proc. of SPIE 2015, pp. 95040N.